10/775068 SHEET 1 OF 1

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO.	SERIAL NO.
		248647US2S CONT	New Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT: Koji SAKUI	
		FILING DATE: Herewith 2/11/04	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
JU	AA	6,434,034	08/2002	Wallace et al.	—	—	
JU	AB	6,278,616	08/2001	Gelsomini et al.	—	—	
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		☐ Additional References sheet(s) attached

Examiner	Vu Le	Date Considered	7/20/04

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.